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DATA SHEET

BST82
N-channel enhancement mode vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

April 1995

Philips Semiconductors

PHILIPS

N-channel enhancement mode vertical D-MOS transistor

BST82

DESCRIPTION

N-channel enhancement mode vertical D-MOS transistor in SOT23 envelope and designed for use as Surface Mounted Device (SMD) in thin and thick-film circuits for telephone ringer and for application with relay, high-speed and line-transformer drivers.

FEATURES

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No second breakdown
- Low $R_{DS(on)}$

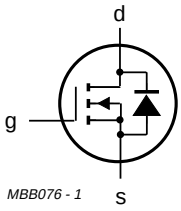
QUICK REFERENCE DATA

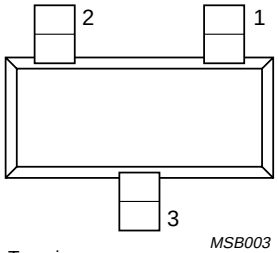
Drain-source voltage	V_{DS}	max.	80	V
Drain-source voltage (non-repetitive peak; $t_p \leq 2$ ms)	$V_{DS(SM)}$	max.	100	V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20	V
Drain current (DC)	I_D	max.	175	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Drain-source ON-resistance				
I_D = 150 mA; V_{GS} = 5 V	$R_{DS(on)}$	typ. max.	7 10	Ω Ω
Transfer admittance				
I_D = 175 mA; V_{DS} = 5 V	$\lvert Y_{fs} \rvert$	typ.	150	mS

PINNING - SOT23

1 = gate
2 = source
3 = drain

PIN CONFIGURATION





Top view

Marking: 02p

Fig.1 Simplified outline and symbol.

N-channel enhancement mode vertical D-MOS transistor

BST82

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	80	V
Drain-source voltage (non-repetitive peak; $t_p \leq 2$ ms)	$V_{DS(SM)}$	max.	100	V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20	V
Drain current (DC)	I_D	max.	175	mA
Drain current (peak)	I_{DM}	max.	600	mA
Total power dissipation up to T_{amb} = 25 °C (note 1)	P_{tot}	max.	300	mW
Storage temperature range	T_{stg}	−65 to +	150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient (note 1)	$R_{th\ j\text{-}a}$	=	430	K/W

Note

1. Transistors mounted on a ceramic substrate of 7 mm x 5 mm x 0.7 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage				
I_D = 10 μA; V_{GS} = 0	$V_{(BR)DSS}$	min.	80	V
Drain-source leakage current				
V_{DS} = 60 V; V_{GS} = 0	I_{DSS}	max.	1.0	μA
Gate-source leakage current				
V_{GS} = 20 V; V_{DS} = 0	I_{GSS}	max.	100	nA
Gate-source cut-off voltage				
I_D = 1 mA; V_{DS} = V_{GS}	$V_{(P)GS}$	min.	1.5	V
		max.	3.5	V
Drain-source ON-resistance				
I_D = 150 mA; V_{GS} = 5 V	$R_{DS(on)}$	typ.	7	Ω
		max.	10	Ω
Transfer admittance				
I_D = 175 mA; V_{DS} = 5 V	$\lvert Y_{fs} \rvert$	typ.	150	mS
Input capacitance at f = 1 MHz				
V_{DS} = 10 V; V_{GS} = 0	C_{iss}	typ.	15	pF
		max.	30	pF
Output capacitance at f = 1 MHz				
V_{DS} = 10 V; V_{GS} = 0	C_{oss}	typ.	13	pF
		max.	20	pF
Feedback capacitance at f = 1 MHz				
V_{DS} = 10 V; V_{GS} = 0	C_{rss}	typ.	3	pF
		max.	6	pF
Switching times (see Figs 2 and 3)				
I_D = 175 mA; V_{DD} = 50 V; V_{GS} = 0 to 10 V	t_{on}	typ.	4	ns
		max.	10	ns
	t_{off}	typ.	4	ns
		max.	10	ns

N-channel enhancement mode vertical D-MOS transistor

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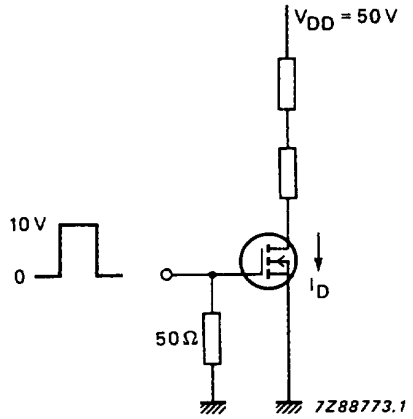


Fig.2 Switching times test circuit.

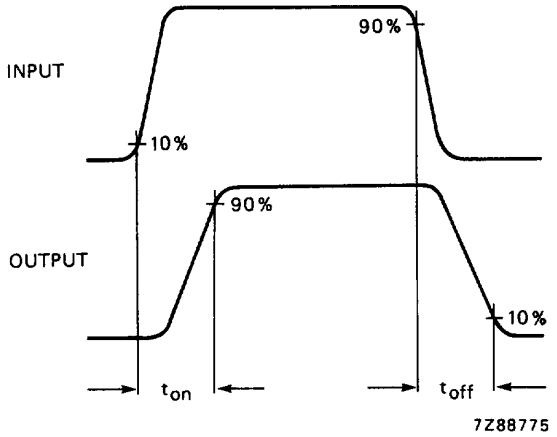


Fig.3 Input and output waveforms.

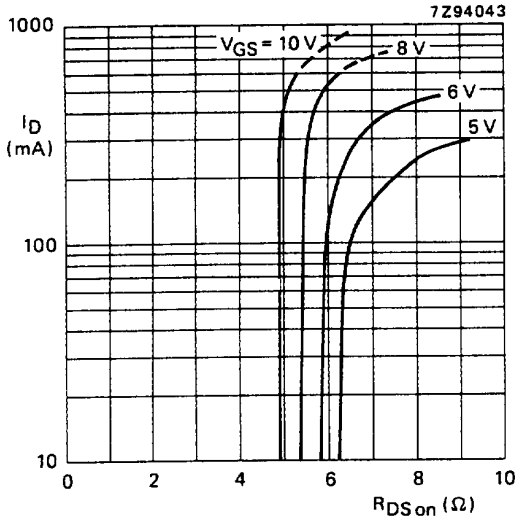


Fig.4 T_j = 25 °C; typical values.

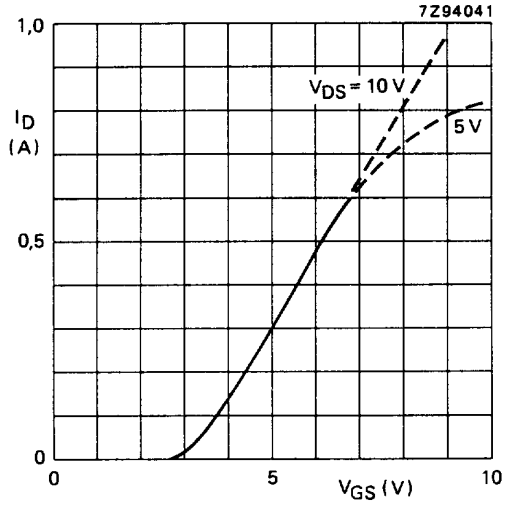


Fig.5 T_j = 25 °C; typical values.

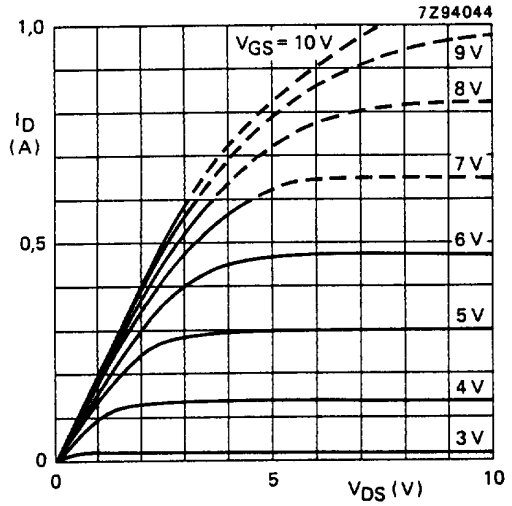


Fig.6 T_j = 25 °C; typical values.

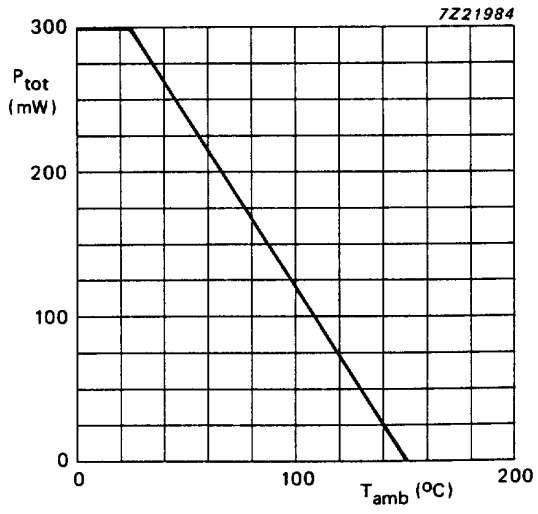


Fig.7 Power derating curve.

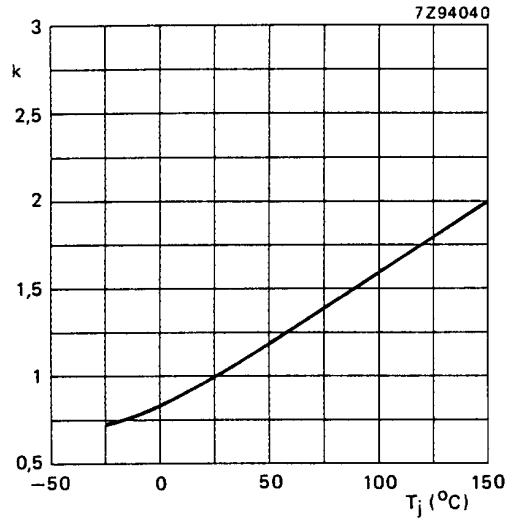


Fig.8

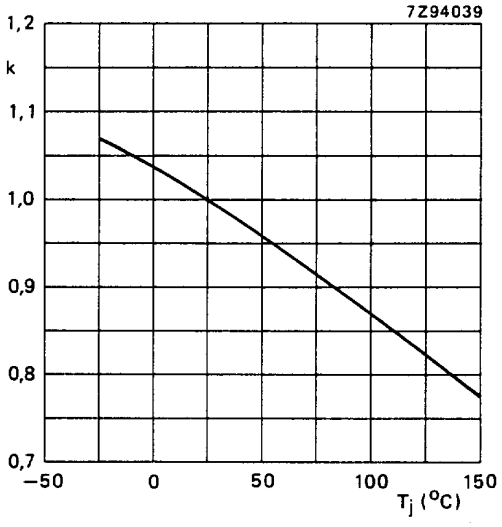


Fig.9

$$k = \frac{V_{GS(th)} \text{ at } T_j}{V_{GS(th)} \text{ at } 25\ °C};$$

$V_{GS(th)}$ at 1 mA; typical values.

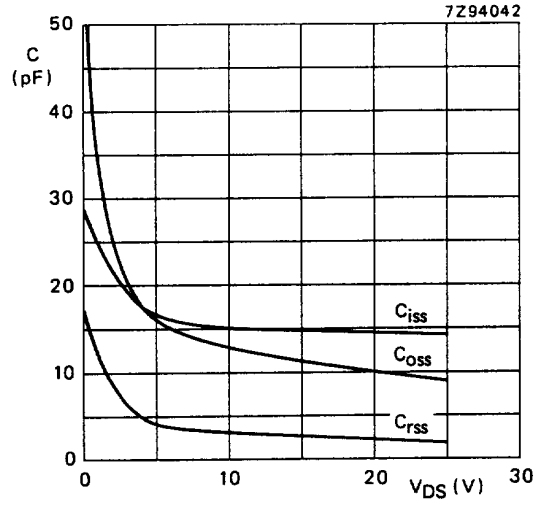
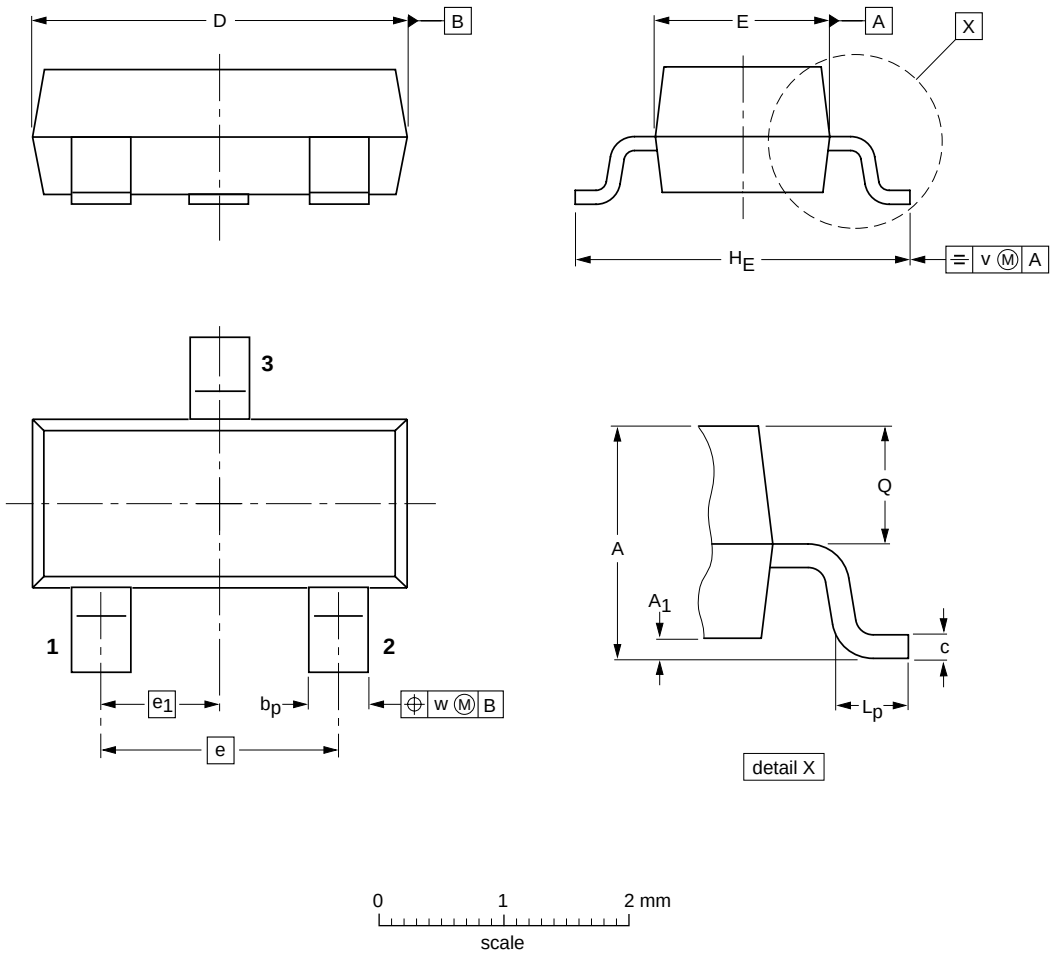


Fig.10 T_j = 25 °C; V_{GS} = 0; f = 1 MHz; typical values.

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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